Standard Rectifier

Phase leg

Part number

DSP8-12S

V_{RRM}	= 2x 1200 V		
I _{FAV}	=	8 A	
V _F	=	1.08 V	



Backside: anode/cathode



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very low forward voltage drop
- Improved thermal behaviour

Applications:

- Diode for main rectification
- For single and three phase
- bridge configurations

Package: TO-263 (D2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Terms Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact the sales office, which is responsible for you. Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact the sales office, which is responsible for you. Should you intend to use the product in aviation, in health or live endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747and per semiconductor unless otherwise specified

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DSP8-12S

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Rectifier				Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit
V _{RSM}	max. non-repetitive reverse bloc	king voltage	$T_{VJ} = 25^{\circ}C$			1300	V
V _{RRM}	max. repetitive reverse blocking	voltage	$T_{VJ} = 25^{\circ}C$			1200	V
I _R	reverse current	$V_{R} = 1200 V$	$T_{VJ} = 25^{\circ}C$			10	μA
		V_{R} = 1200 V	$T_{VJ} = 150^{\circ}C$			0.2	mA
V _F	forward voltage drop	I _F = 8 A	$T_{VJ} = 25^{\circ}C$			1.16	V
		I _F = 16 A				1.35	V
		I _F = 8 A	T _{vj} = 150 °C			1.08	V
		$I_{F} = 16 \text{ A}$				1.34	V
FAV	average forward current	T _c = 160°C	T _{vJ} = 175°C			8	Α
		rectangular d = 0.5					
V _{F0}	threshold voltage		T _{vJ} = 175°C			0.79	V
r _F	slope resistance } for power	loss calculation only				33	mΩ
R _{thJC}	thermal resistance junction to ca	ase				1.5	K/W
R _{thCH}	thermal resistance case to heats	sink			0.25		K/W
P _{tot}	total power dissipation		$T_c = 25^{\circ}C$			100	W
IFSM	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			120	Α
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			130	Α
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150$ °C			100	Α
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			110	Α
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			72	A²s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			70	A²s
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 150$ °C			50	A ² s
		t = 8,3 ms; (60 Hz), sine	$V_{R} = 0 V$			50	A²s
C	junction capacitance	V_{R} = 400 V; f = 1 MHz	$T_{VJ} = 25^{\circ}C$		4		pF

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DSP8-12S

Package	Package TO-263 (D2Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal			25	Α	
T _{vj}	virtual junction temperature		-55		175	°C	
T _{op}	operation temperature		-55		150	°C	
T _{stg}	storage temperature		-55		150	°C	
Weight				2		g	
F _c	mounting force with clip		20		60	Ν	

Product Marking



Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSP8-12S	DSP8-12S	Tape & Reel	800	499390
Alternative	DSP8-12S-TUB	DSP8-12S	Tube	50	499382

Similar Part	Package	Voltage class
DSP8-12AS	TO-263AA (D2Pak) (3)	1200
DSP8-12A	TO-220AB (3)	1200
DSP8-12AC	ISOPLUS220AB (3)	1200
DSP8-08S	TO-263AB (D2Pak) (2)	800
DSP8-08AS	TO-263AA (D2Pak) (3)	800
DSP8-08A	TO-220AB (3)	800

Equiva	lent Circuits for	Simulation	* on die level	$T_{vJ} = 175 ^{\circ}C$
	- R _o -	Rectifier		
V _{0 max}	threshold voltage	0.79		V
$\mathbf{R}_{0 \text{ max}}$	slope resistance *	30		mΩ

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Outlines TO-263 (D2Pak)



Dim.	Millimeter		Inches	
D	min	max	min	max
Α	4.06	4.83	0.160	0.190
A1	typ.	0.10	typ. 0.004	
A2	2.	41	0.0	95
b	0.51	0.99	0.020	0.039
b2	1.14	1.40	0.045	0.055
С	0.40	0.74	0.016	0.029
c2	1.14	1.40	0.045	0.055
D	8.38	9.40	0.330	0.370
D1	8.00	8.89	0.315	0.350
D2	2	.5	0.098	
Е	9.65	10.41	0.380	0.410
E1	6.22	8.50	0.245	0.335
е	2,54 BSC		0,100	BSC
e1	4.28		0.1	69
Н	14.61	15.88	0.575	0.625
L	1.78	2.79	0.070	0.110
L1	1.02	1.68	0.040	0.066
W	typ. 0.02	0.040	typ. 0.0008	0.002
All dimensions conform with				

and/or within JEDEC standard.



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Rectifier



Fig. 1 Forward current versus

voltage drop per diode



Fig. 2 Surge overload current



Fig. 3 I²t versus time per diode

DC =

1

0.5

0.4

0.33

0.17

0.08

28

24

20

16

12

8

4

0

i

2 0.332

4 0.3

1 0.155

3 0.713

5 0.00001

R_{thi} (K/W)

0

50

100

т_с [°С]

Fig. 5 Max. forward current vs. case temperature

t_i (s)

0.0005

0.0095

0.17

0.8

0.00001

Constants for Z_{thJC} calculation:

150

200

I_{F(AV)M}

[A]



Fig. 4 Power dissipation vs. direct output current and ambient temperature







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